
PF0411

MOS FET Power Amplifier Module for PCS1900 Handy Phone

HITACHI

ADE-208-325A (Z)
2nd. Edition
July 1996

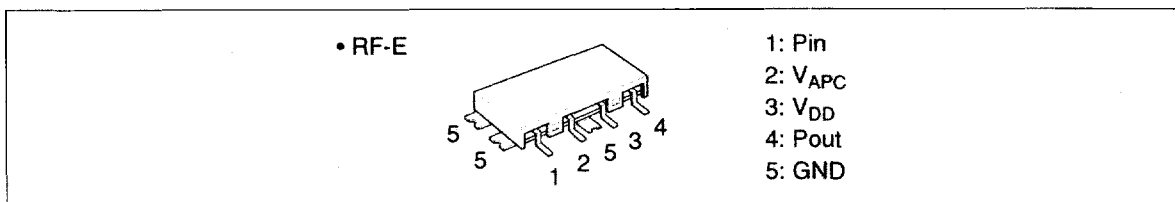
Application

For PCS 1900 class 1: 1850 to 1910 MHz

Features

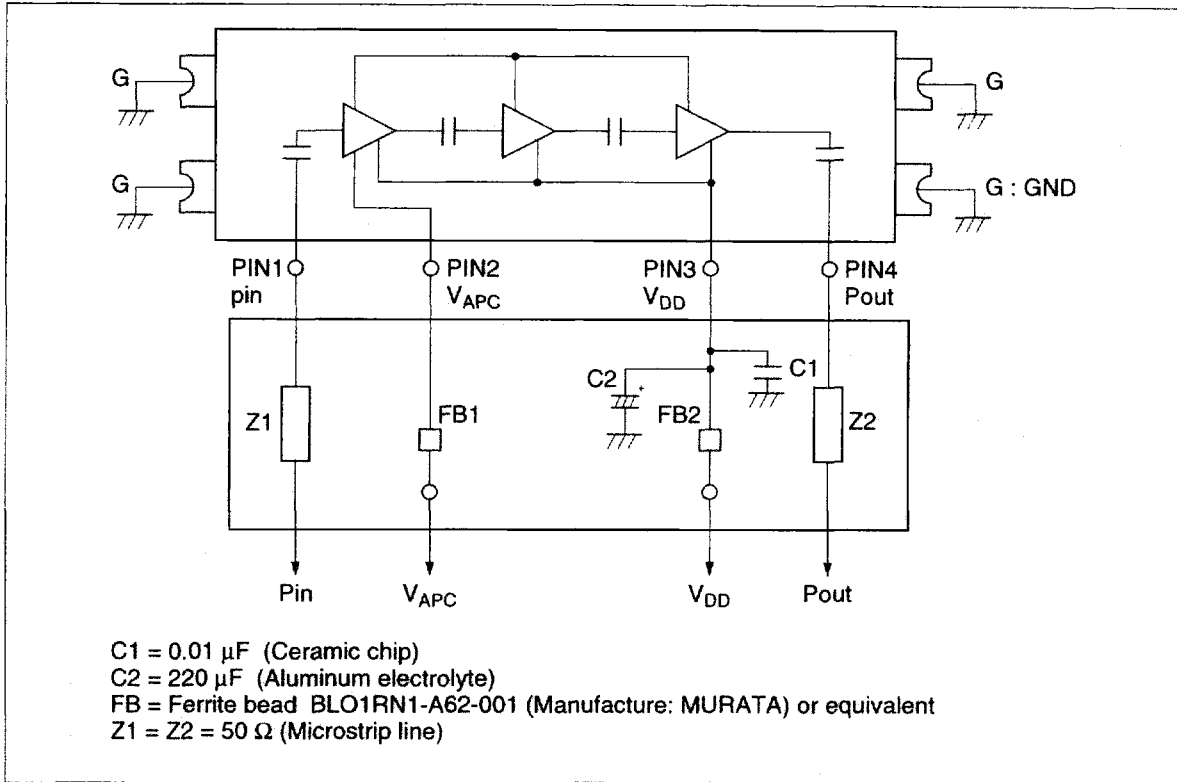
- Small package: 1 cc, 3g
- High efficiency: 32% Typ
- High speed switching: 0.9 μ sec

Pin Arrangement



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Internal Diagram and External Circuit



Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

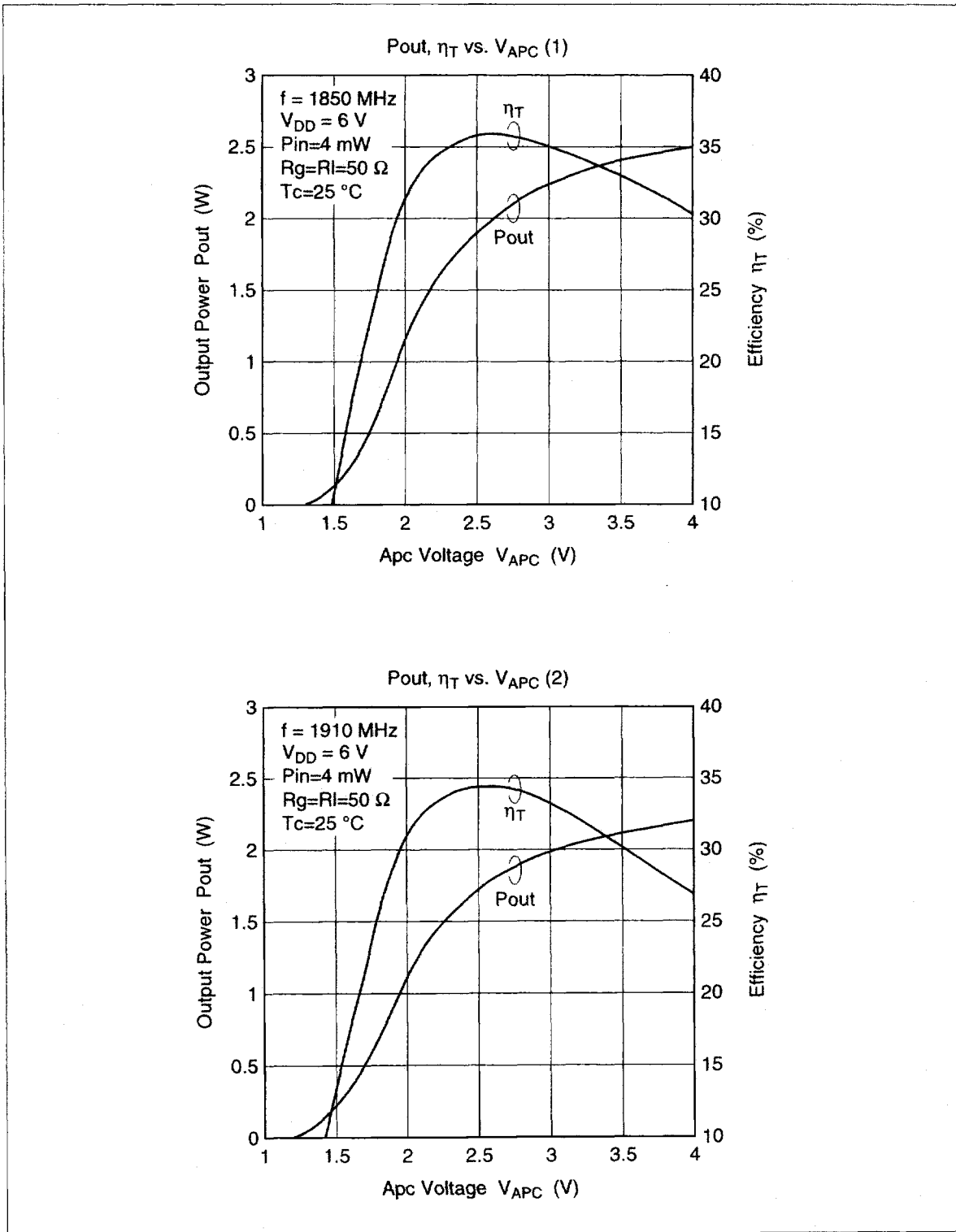
Item	Symbol	Rating	Unit
Supply voltage	VDD	10	V
Supply current	IDD	2	A
VAPC voltage	VAPC	6	V
Input power	Pin	20	mW
Operating case temperature	T_c (op)	-30 to +100	$^\circ\text{C}$
Storage temperature	T_{stg}	-30 to +100	$^\circ\text{C}$
Output power	Pout	3	W

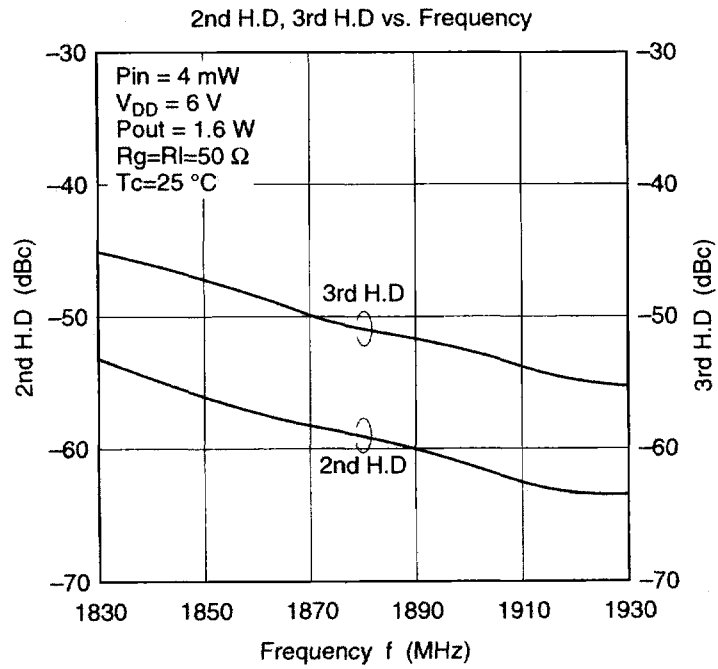
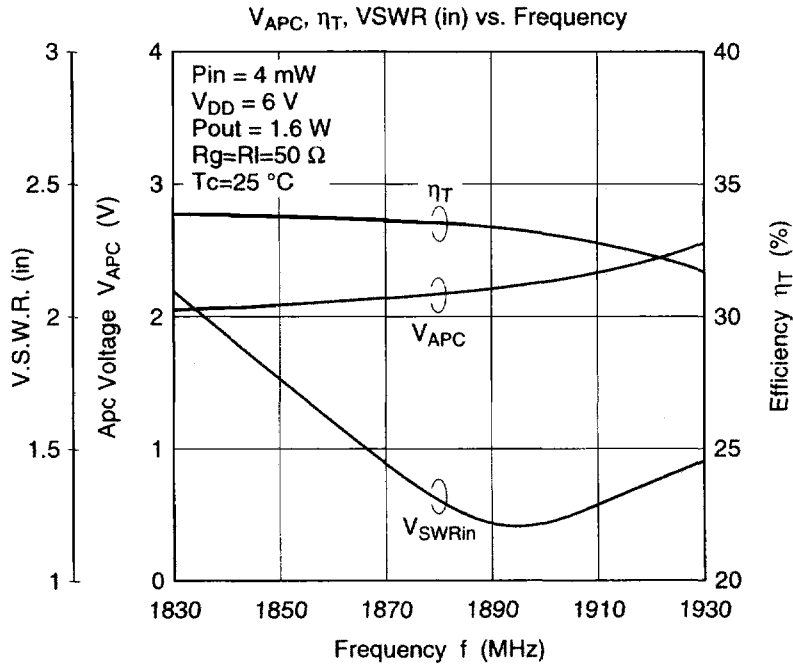
Electrical Characteristics (Tc = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	1850	—	1910	MHz	—
Control Voltage range	VAPC	0.5	—	4.0	V	—
Drain cutoff current	IDS	—	—	100	μA	VDD = 10 V, VAPC = 0 V
Total efficiency	ηT	28	33	—	%	Pin = 4 mW, VDD = 6 V,
2nd harmonic distortion	2nd H.D.	—	-50	-30	dBc	Pout = 1.6 W (at APC controlled),
3rd harmonic distortion	3rd H.D.	—	-50	-30	dBc	RL = Rg = 50 Ω, Tc = 25°C
Input VSWR	VSWR (in)	—	2	3	—	
Output power (1)	Pout (1)	1.7	2.0	—	W	Pin = 4 mW, VDD = 6 V, VAPC = 4 V, RL = Rg = 50 Ω, Tc = 25°C
Output power (2)	Pout (2)	1.0	1.2	—	W	Pin = 4 mW, VDD = 5.4 V, VAPC = 4 V, RL = Rg = 50 Ω, Tc = 80°C
Isolation	—	—	-35	-30	dBm	Pin = 4 mW, VDD = 6 V, VAPC = 0.5 V, RL = Rg = 50 Ω
Switching time	tr, tf	—	-0.9	2	μs	Pin = 4 mW, VDD = 6 V, Pout = 1.6 W, RL = Rg = 50 Ω, Tc = 25°C
Stability	—	No parasitic			—	Pin = 4 mW, VDD = 7.5 V, Pout ≤ 1.6 W, (at APC controlled), Rg = 50 Ω, Tc = 25°C, Output VSWR = 10:1 All phases

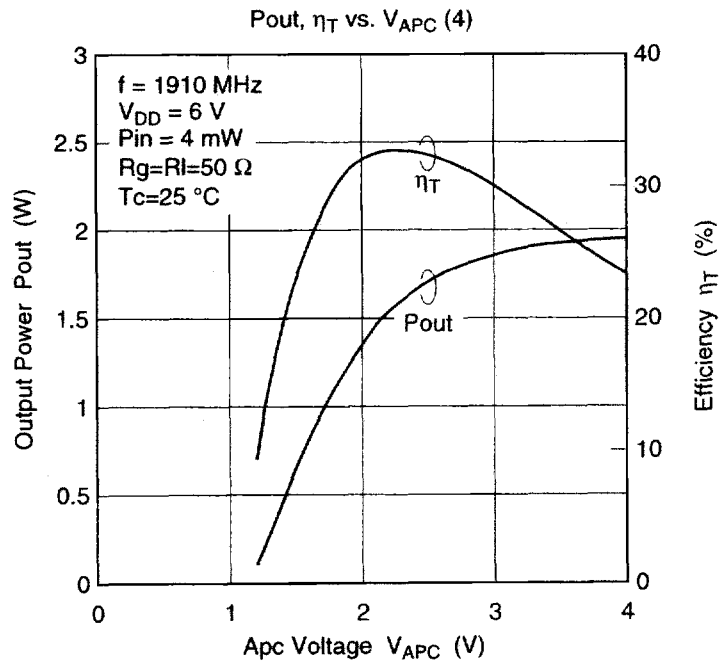
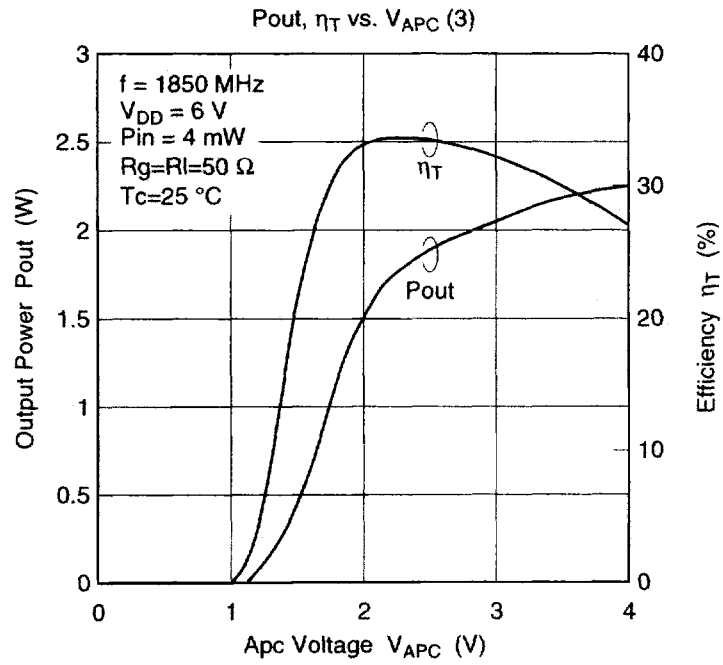
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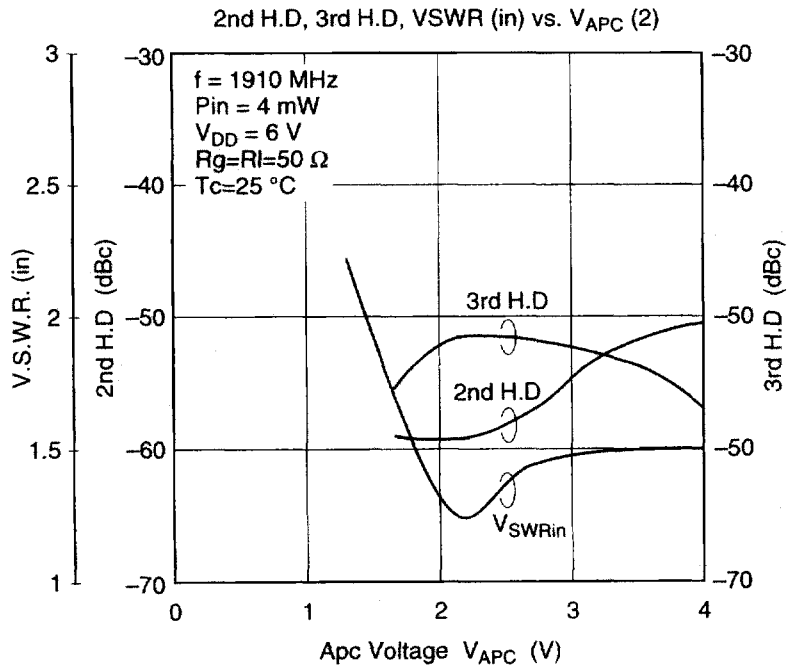
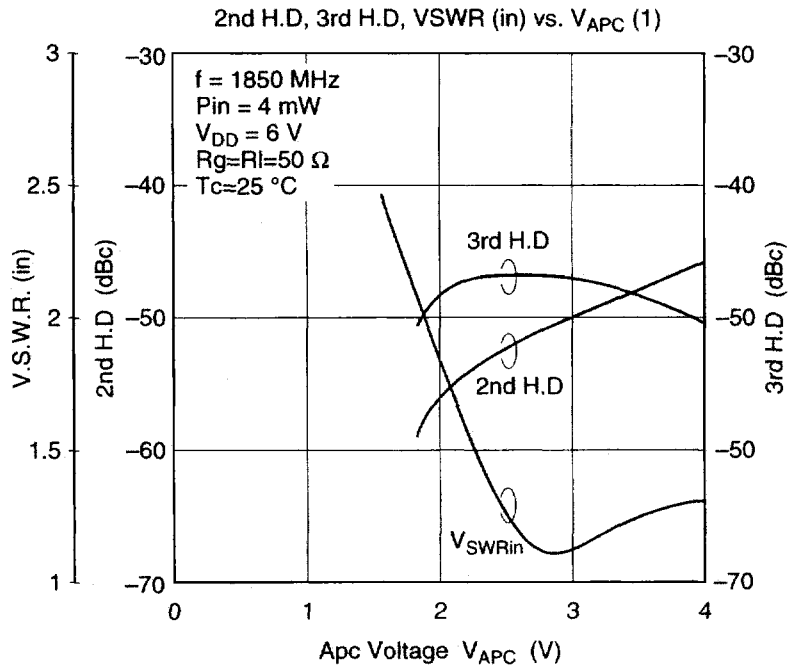
Characteristics Curve



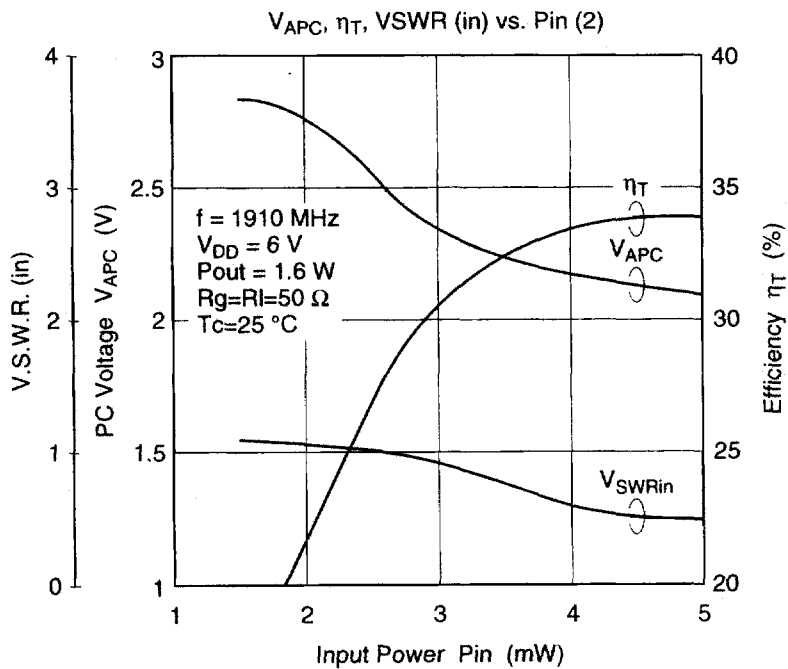
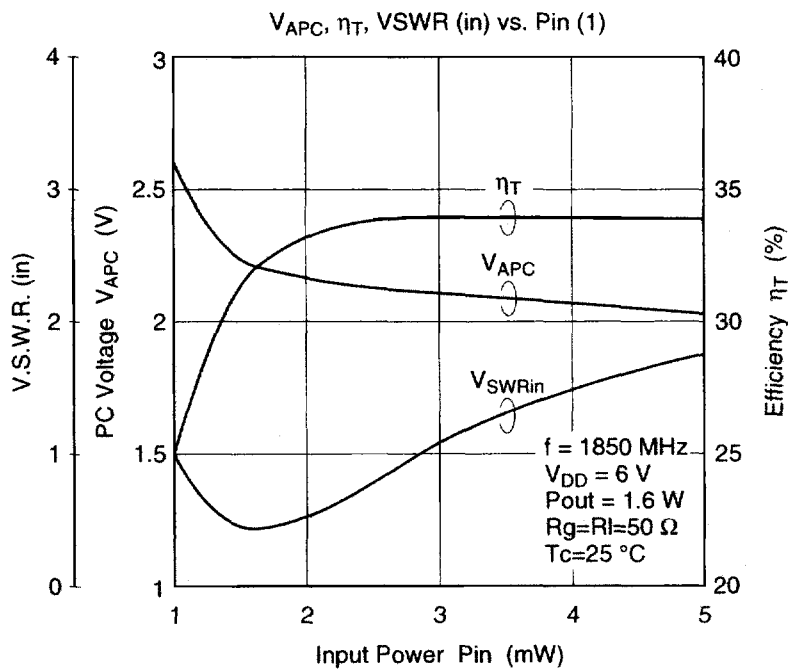


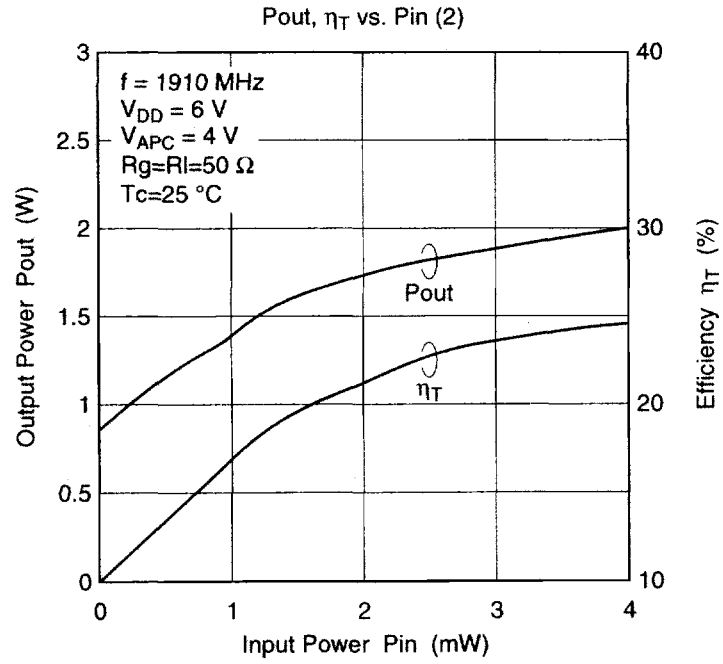
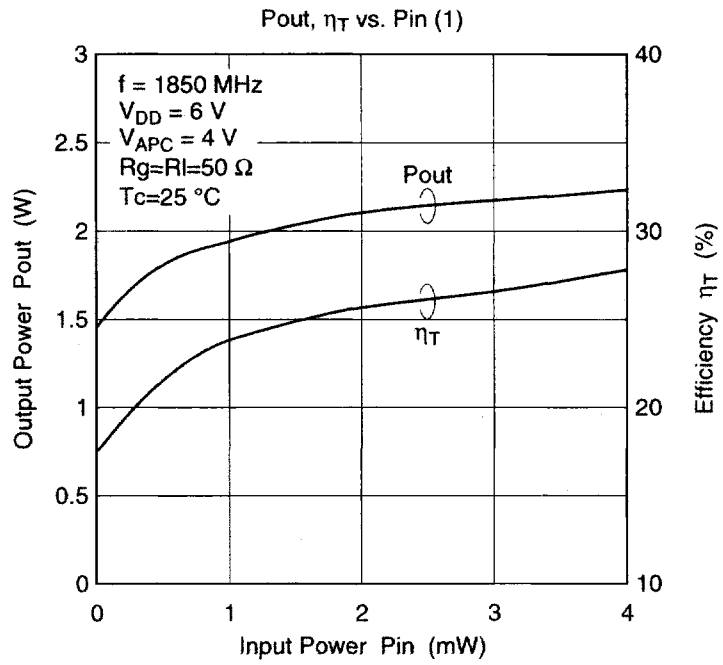
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